

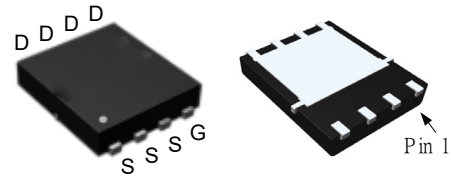
Features

- 80V/-80A
 - $R_{DS(ON)}=10\text{m}\Omega(\text{typ.})@V_{GS}=-10\text{V}$
 - $R_{DS(ON)}=12\text{m}\Omega(\text{typ.})@V_{GS}=-4.5\text{V}$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Moisture Sensitivity Level MSL1 (per JEDEC J-STD-020D)

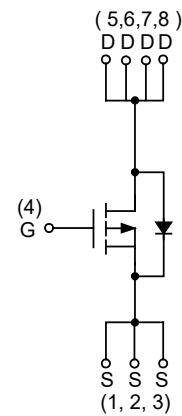
Applications

- DC/DC Converter.
- Power Management.
- Load Switch.
- Portable Equipment and Battery Powered Systems.

Pin Description



DFN5x6A-8_EP



P-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-80	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	-80	A
I _D	Continuous Drain Current	T _C =25°C	-80	A
		T _C =100°C	-60	
I _{DM}	Pulsed Drain Current	T _C =25°C	-240	
P _D	Maximum Power Dissipation	T _C =25°C	89.3	W
		T _C =100°C	35.7	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	1.4	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient	Steady State	55	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	-28	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	196	mJ

Note a : Pulse width limited by maximum junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature (initial temperature $T_J=25^{\circ}\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

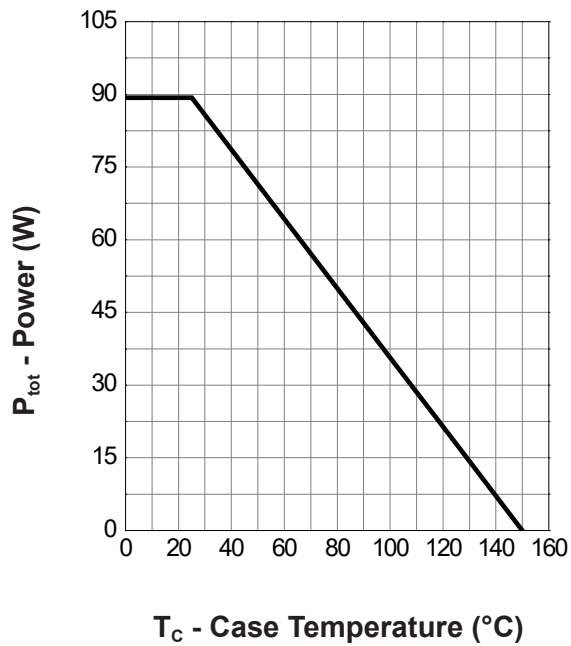
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-80	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-64V, V _{GS} =0V T _J =85°C	-	-	-1	μA
			-	-	-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1	-1.5	-2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^c	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-25A	-	10	13	mΩ
		V _{GS} =-4.5V, I _{DS} =-20A	-	12	15	
Diode Characteristics						
V _{SD} ^c	Diode Forward Voltage	I _{SD} =-12A, V _{GS} =0V	-	-0.8	-1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-25A, dI _{SD} /dt=100A/μs	-	39	-	ns
Q _{rr}	Reverse Recovery Charge		-	62	-	nC
Dynamic Characteristics ^d						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-30V, Frequency=1.0MHz	-	4800	6240	pF
C _{oss}	Output Capacitance		-	350	-	
C _{rss}	Reverse Transfer Capacitance		-	185	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-30V, R _L =30Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	23	41	ns
t _r	Turn-on Rise Time		-	18	32	
t _{d(OFF)}	Turn-off Delay Time		-	115	207	
t _f	Turn-off Fall Time		-	47	85	
Gate Charge Characteristics ^d						
Q _g	Total Gate Charge	V _{DS} =-30V, V _{GS} =-10V, I _{DS} =-25A	-	90	126	nC
Q _{gs}	Gate-Source Charge		-	19	-	
Q _{gd}	Gate-Drain Charge		-	24	-	

Note c : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

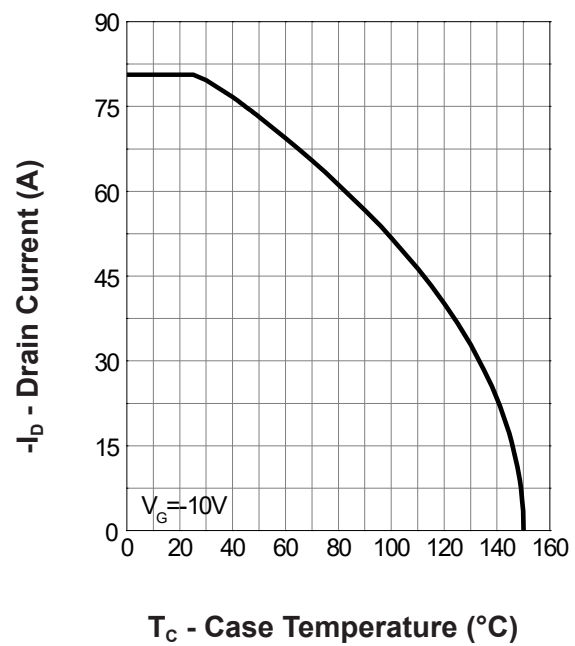
Note d : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

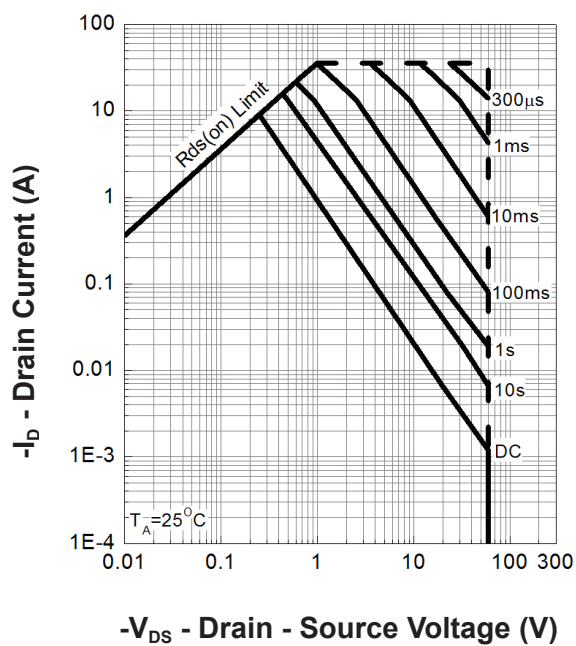
Power Dissipation



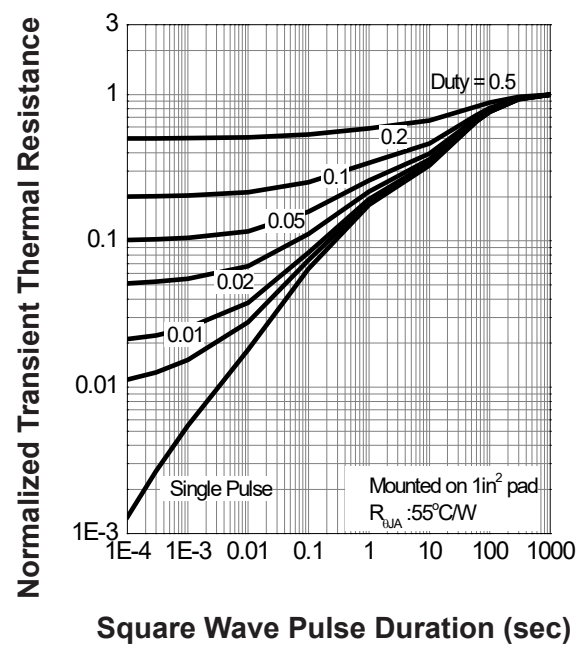
Drain Current



Safe Operation Area

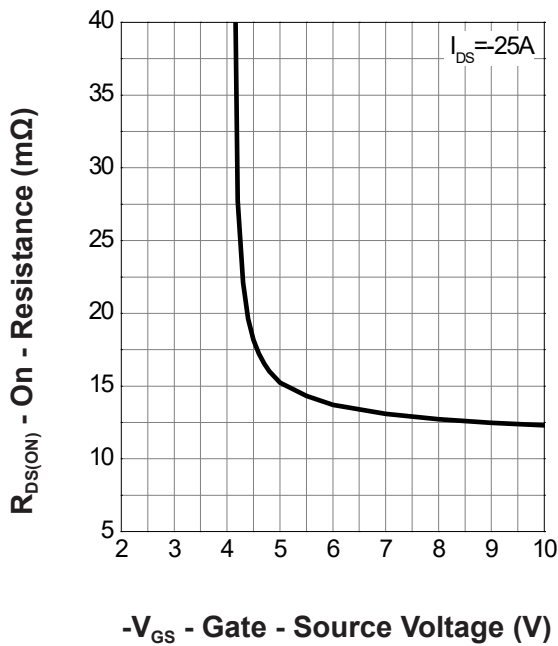


Thermal Transient Impedance

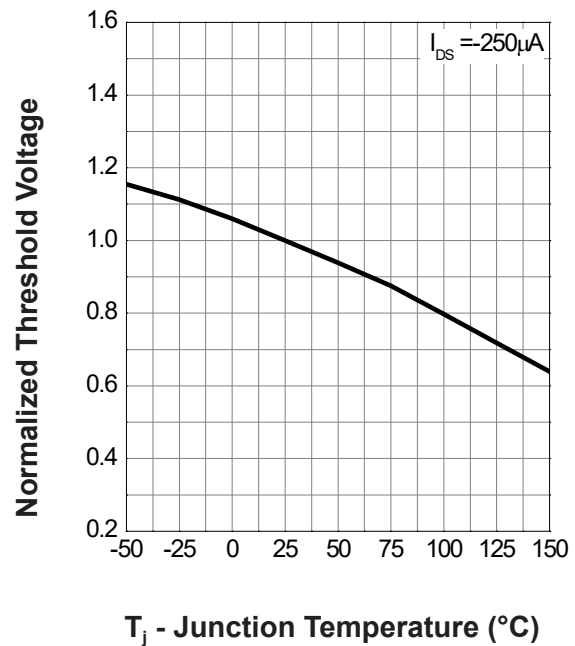


Typical Operating Characteristics(Cont.)

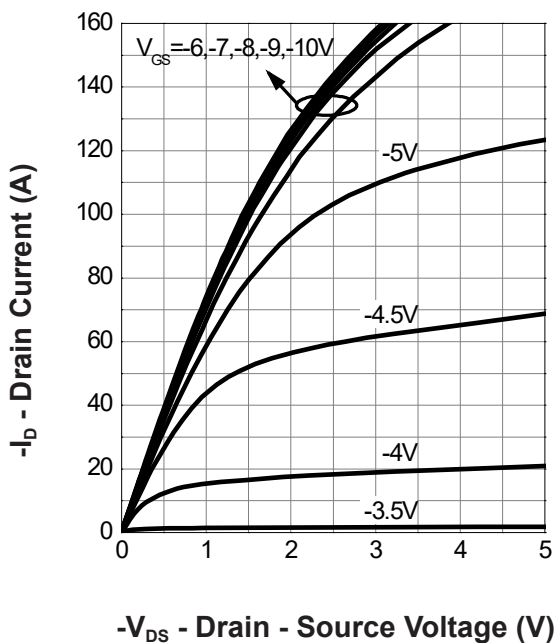
Gate-Source On Resistance



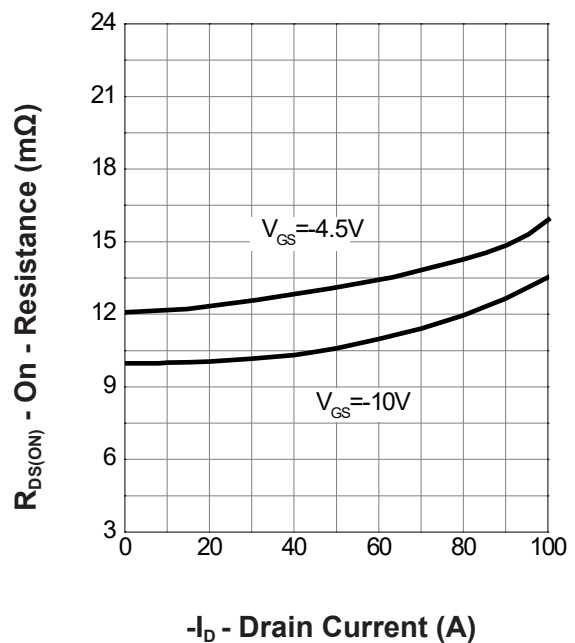
Gate Threshold Voltage



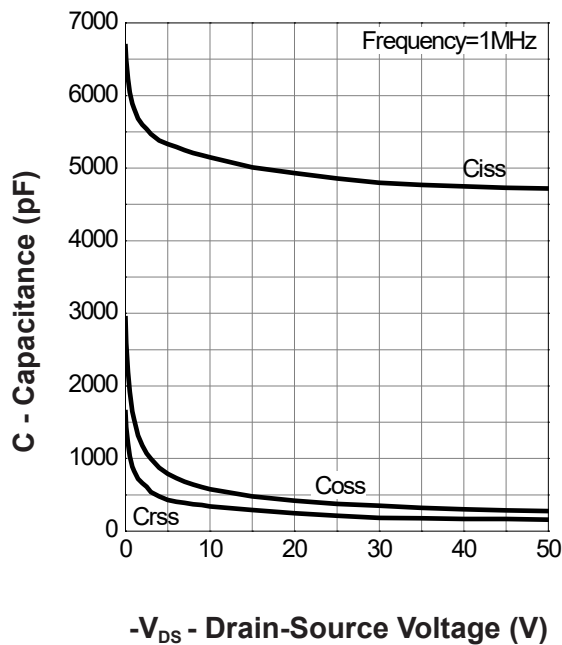
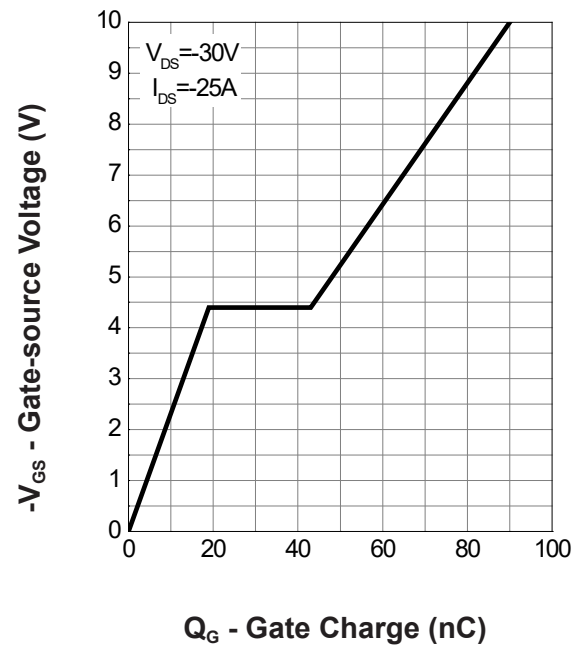
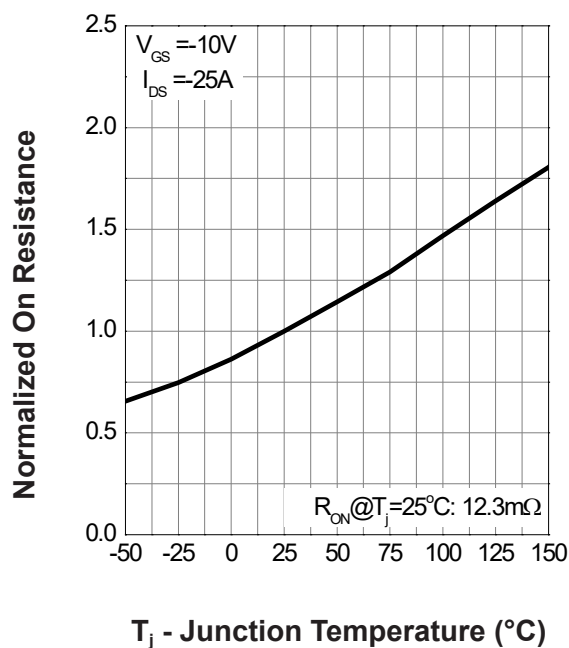
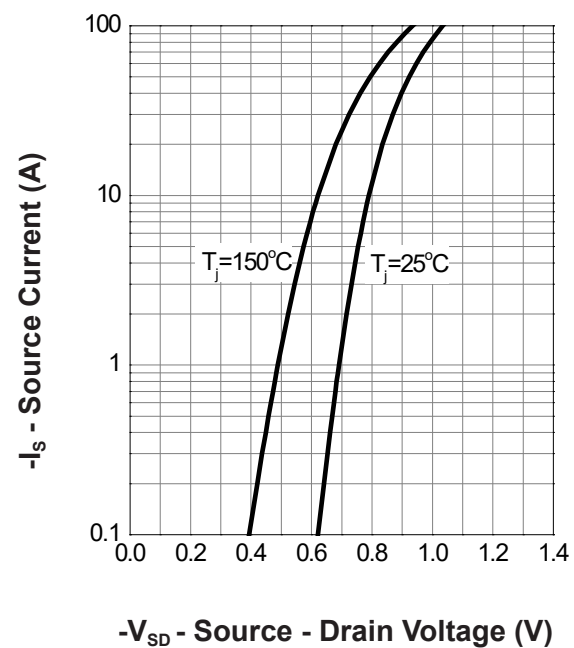
Output Characteristics



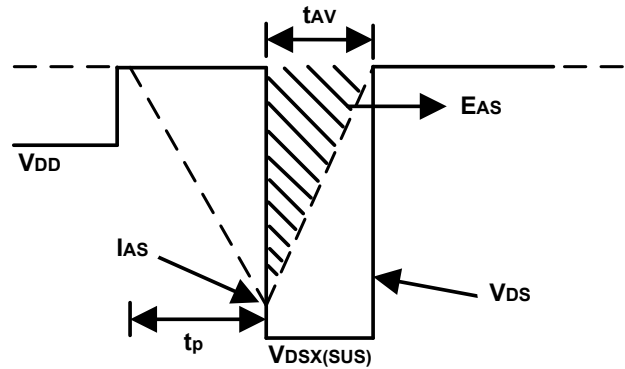
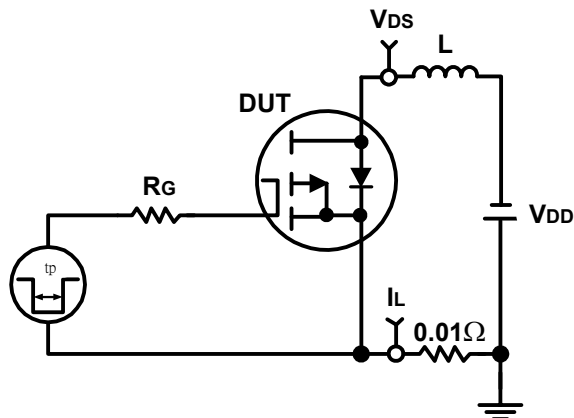
Drain-Source On Resistance



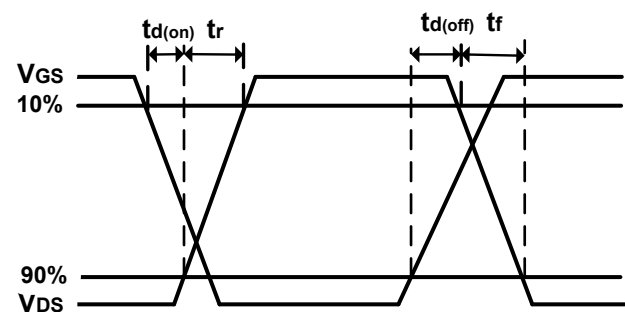
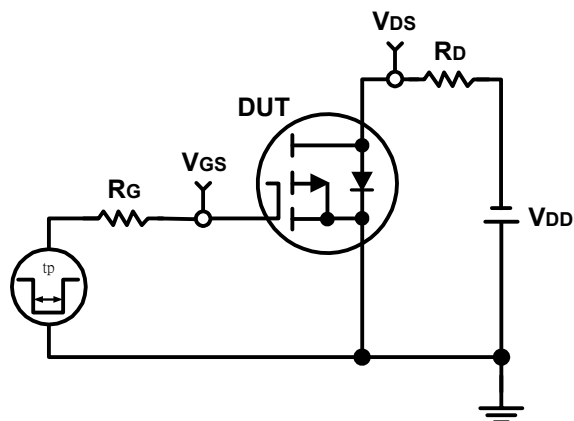
Typical Operating Characteristics(Cont.)

Capacitance

Gate Charge

Drain-Source On Resistance

Source-Drain Diode Forward


Avalanche Test Circuit and Waveforms

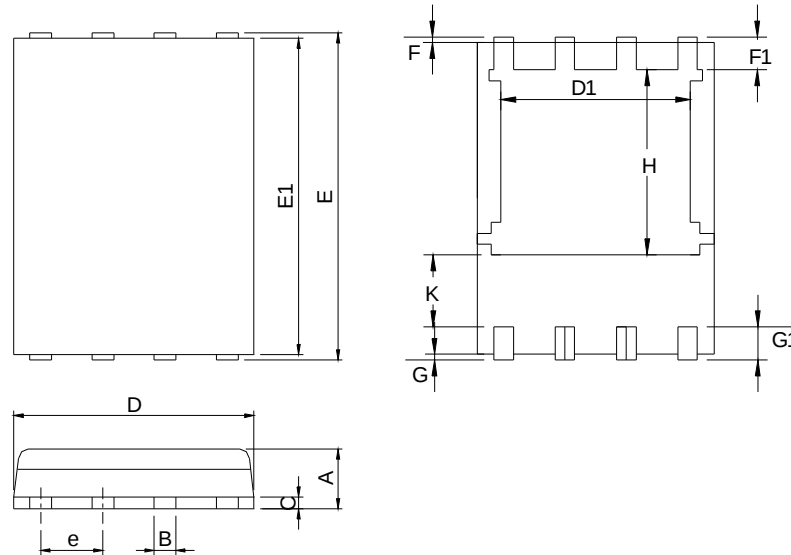


Switching Time Test Circuit and Waveforms



Package Information

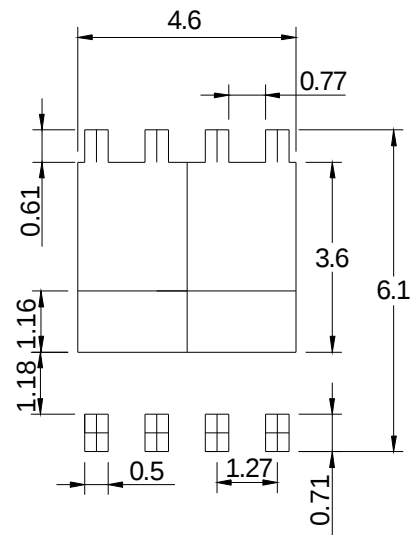
DFN5x6-8



SYMBOL	DFN5x6-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.20	0.035	0.047
B	0.3	0.51	0.012	0.020
C	0.19	0.25	0.007	0.010
D	4.80	5.30	0.189	0.209
D1	4.00	4.40	0.157	0.173
E	5.90	6.20	0.232	0.244
E1	5.50	5.80	0.217	0.228
e	1.27 BSC		0.050 BSC	
F	0.05	0.30	0.002	0.012
F1	0.35	0.75	0.014	0.030
G	0.05	0.30	0.002	0.012
G1	0.35	0.75	0.014	0.030
H	3.34	3.9	0.131	0.154
K	0.762	-	0.03	-

Note : 1.Dimension D, D1,D2 and E1 do not include mold flash or protrusions.
Mold flash or protrusions shall not exceed 10 mil.

RECOMMENDED LAND PATTERN



UNIT: mm